

SKiiP 14AC12T7V1



MiniSKiiP® 1

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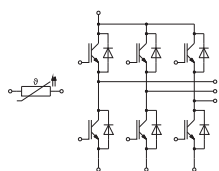
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Features*

- 1200V Generation 7 IGBTs (T7)
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Remarks

- Max. case temperature limited to $T_C = T_S = 125^\circ\text{C}$
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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
Inverter - IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$\lambda_{paste}=0.8\text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	A
	$T_j = 175^\circ\text{C}$	$T_s = 100^\circ\text{C}$	A
I_C	$\lambda_{paste}=2.5\text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	A
	$T_j = 175^\circ\text{C}$	$T_s = 100^\circ\text{C}$	A
I_{Cnom}		35	A
I_{CRM}		70	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 175^\circ\text{C}$	μs
T_j		-40 ... 175	$^\circ\text{C}$
Inverse - Diode			
V_{RRM}	$T_j = 25^\circ\text{C}$	1200	V
I_F	$\lambda_{paste}=0.8\text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	A
	$T_j = 175^\circ\text{C}$	$T_s = 100^\circ\text{C}$	A
I_F	$\lambda_{paste}=2.5\text{ W/(mK)}$	$T_s = 70^\circ\text{C}$	A
	$T_j = 175^\circ\text{C}$	$T_s = 100^\circ\text{C}$	A
I_{FRM}		70	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$	170	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}, 20\text{ A per spring}$	40	A
T_{stg}	module without TIM	-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	2500	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 35\text{ A}$	$T_j = 25^\circ\text{C}$	1.60	1.75	V
	$V_{GE} = 15\text{ V}$	$T_j = 150^\circ\text{C}$	1.78	1.93	V
	chiplevel	$T_j = 175^\circ\text{C}$	1.82	1.97	V
V_{CE0}		$T_j = 25^\circ\text{C}$	1.00	1.05	V
	chiplevel	$T_j = 150^\circ\text{C}$	0.80	0.85	V
		$T_j = 175^\circ\text{C}$	0.75	0.80	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	17	20	$\text{m}\Omega$
	chiplevel	$T_j = 150^\circ\text{C}$	28	31	$\text{m}\Omega$
		$T_j = 175^\circ\text{C}$	31	33	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0.75\text{ mA}$	5.15	5.8	6.45	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_j = 25^\circ\text{C}$			1	mA
C_{ies}	$V_{CE} = 25\text{ V}$	$f = 1\text{ MHz}$	6.60		nF
C_{oes}	$V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.09		nF
C_{res}		$f = 1\text{ MHz}$	0.02		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		490		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0		Ω

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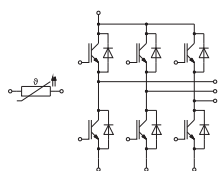
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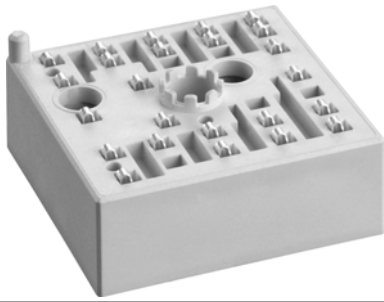


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Characteristics					
Symbol	Conditions		min.	typ.	max. Unit
Inverter - IGBT					
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 35\text{ A}$ $R_{G\ on} = 9.1\ \Omega$ $R_{G\ off} = 9.1\ \Omega$ $V_{GE} = +15/-15\text{ V}$	$T_j = 25^\circ\text{C}$		37	ns
		$T_j = 150^\circ\text{C}$		39	ns
		$T_j = 175^\circ\text{C}$		40	ns
t_r		$T_j = 25^\circ\text{C}$		37	ns
		$T_j = 150^\circ\text{C}$		43	ns
		$T_j = 175^\circ\text{C}$		46	ns
E_{on}		$T_j = 25^\circ\text{C}$		3.1	mJ
		$T_j = 150^\circ\text{C}$		4.4	mJ
		$T_j = 175^\circ\text{C}$		4.6	mJ
$t_{d(off)}$		$T_j = 25^\circ\text{C}$		231	ns
		$T_j = 150^\circ\text{C}$		321	ns
		$T_j = 175^\circ\text{C}$		346	ns
t_f	$@ T_j = 150^\circ\text{C}$: $di/dt_{on} = 860\text{ A}/\mu\text{s}$ $di/dt_{off} = 380\text{ A}/\mu\text{s}$ $dv/dt = 3610\text{ V}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		48	ns
		$T_j = 150^\circ\text{C}$		74	ns
		$T_j = 175^\circ\text{C}$		90	ns
E_{off}		$T_j = 25^\circ\text{C}$		2.3	mJ
		$T_j = 150^\circ\text{C}$		3.9	mJ
		$T_j = 175^\circ\text{C}$		4.2	mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W}/(\text{mK})$			0.92	K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 2.5\text{ W}/(\text{mK})$			0.76	K/W

Characteristics					
Symbol	Conditions		min.	typ.	max. Unit
Inverse - Diode					
$V_F = V_{EC}$	$I_F = 35\text{ A}$ $V_{GE} = 0\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$		2.30	2.62 V
		$T_j = 150^\circ\text{C}$		2.29	2.62 V
		$T_j = 175^\circ\text{C}$		2.14	2.46 V
V_{F0}	chiplevel	$T_j = 25^\circ\text{C}$		1.30	1.50 V
		$T_j = 150^\circ\text{C}$		0.90	1.10 V
		$T_j = 175^\circ\text{C}$		0.82	0.98 V
r_F	chiplevel	$T_j = 25^\circ\text{C}$		29	32 mΩ
		$T_j = 150^\circ\text{C}$		40	43 mΩ
		$T_j = 175^\circ\text{C}$		38	42 mΩ
I_{RRM}	$I_F = 35\text{ A}$ $V_{GE} = +15/-15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 25^\circ\text{C}$		22	A
		$T_j = 150^\circ\text{C}$		28	A
		$T_j = 175^\circ\text{C}$		33	A
Q_{rr}		$T_j = 25^\circ\text{C}$		2	μC
		$T_j = 150^\circ\text{C}$		5.2	μC
		$T_j = 175^\circ\text{C}$		5.7	μC
E_{rr}	$@ T_j = 150^\circ\text{C}$: $di/dt_{off} = 870\text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		0.61	mJ
		$T_j = 150^\circ\text{C}$		2	mJ
		$T_j = 175^\circ\text{C}$		2.6	mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8\text{ W}/(\text{mK})$			1.1	K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 2.5\text{ W}/(\text{mK})$			0.93	K/W
Module					
L_{CE}				-	nH
M_s	to heat sink		2		2.5 Nm
w				30	g

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Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
Temperature Sensor					
R_{100}	$T_r=100^{\circ}\text{C}$ ($R_{25}=1000\Omega$)		$1670 \pm 3\%$		Ω
$R_{(T)}$	$R_{(T)}=1000\Omega[1+A(T-25^{\circ}\text{C})+B(T-25^{\circ}\text{C})^2]$, $A = 7.635 \cdot 10^{-3}^{\circ}\text{C}^{-1}$, $B = 1.731 \cdot 10^{-5}^{\circ}\text{C}^{-2}$				

Creepage distance (spring to spring) between temperature sensor and phase W = 2.9mm (CTI 600)

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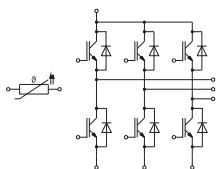
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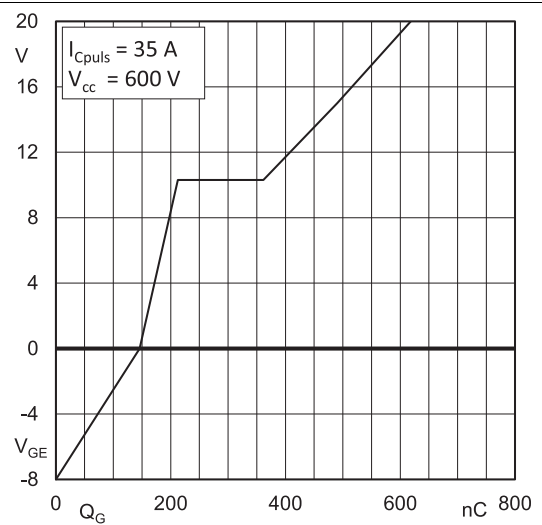
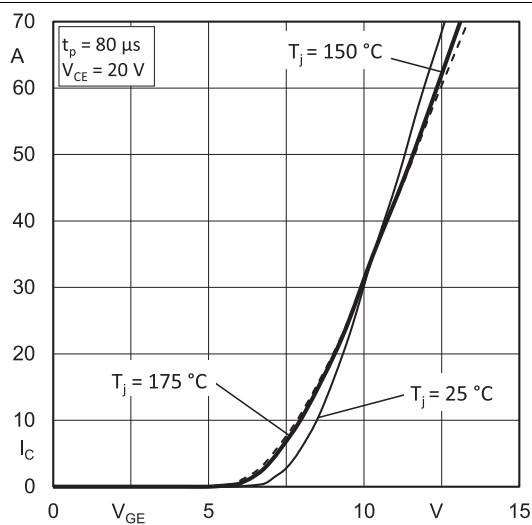
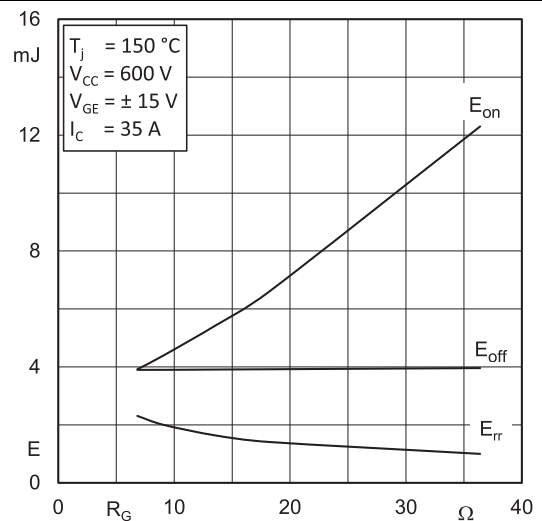
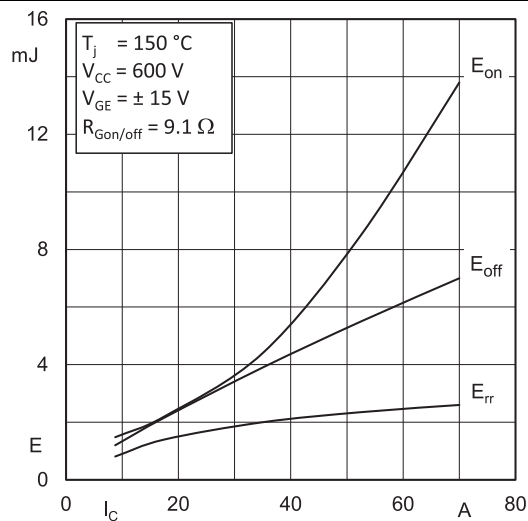
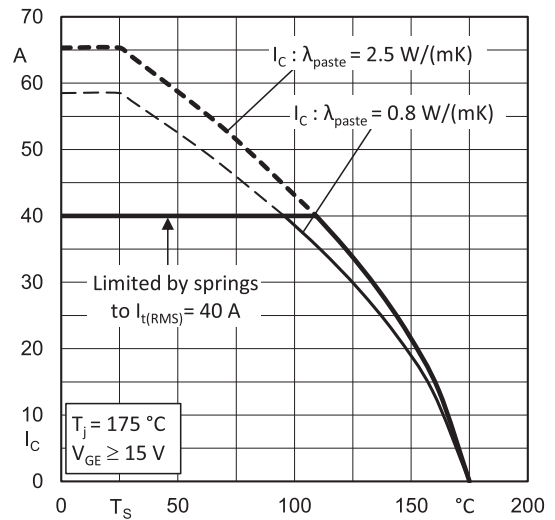
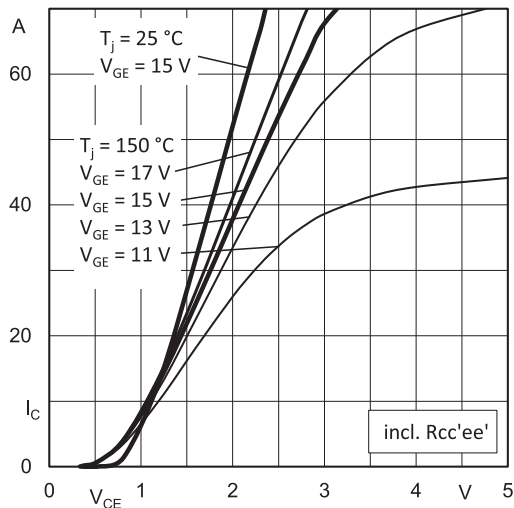
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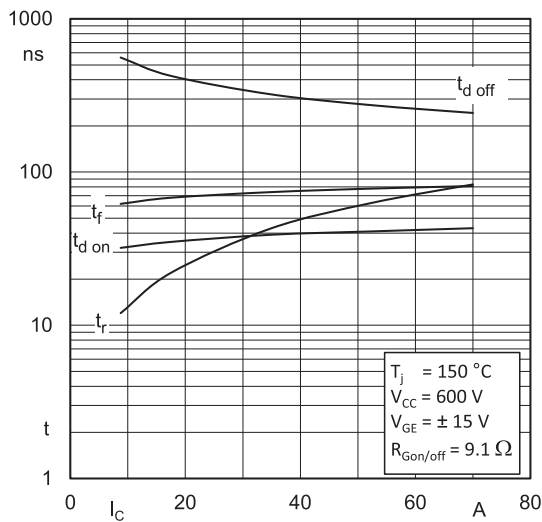


Fig. 7: Typ. switching times vs. I_C

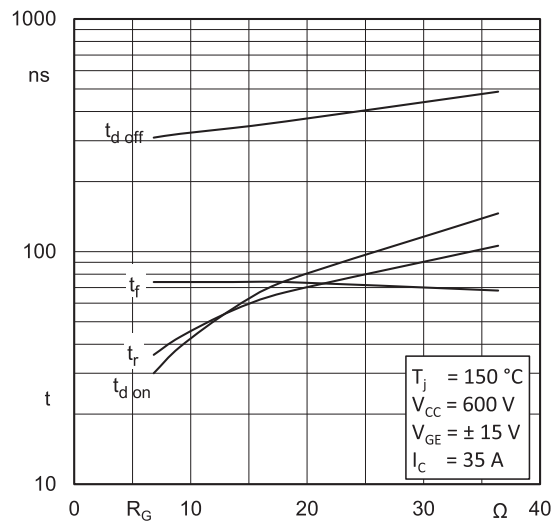


Fig. 8: Typ. switching times vs. gate resistor R_G

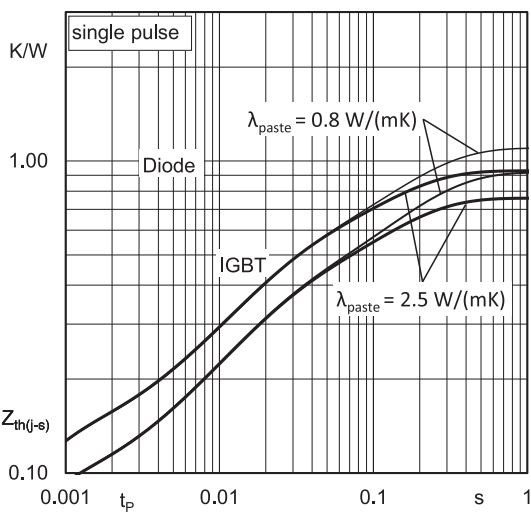


Fig. 9: Typ. transient thermal impedance

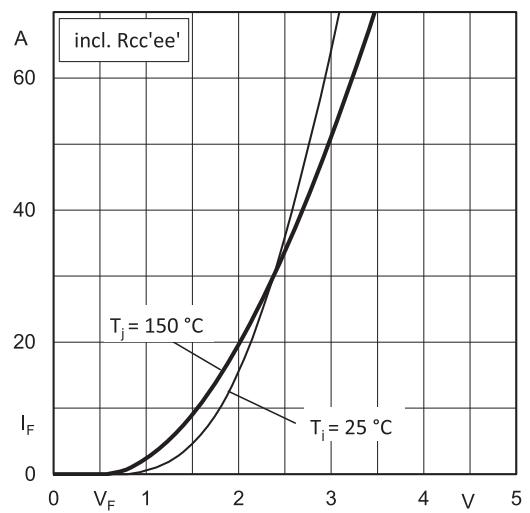


Fig. 10: Typ. CAL diode forward characteristic

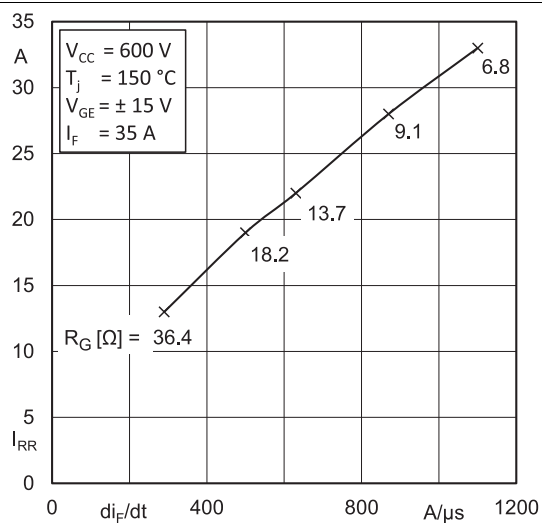


Fig. 11: Typ. CAL diode peak reverse recovery current

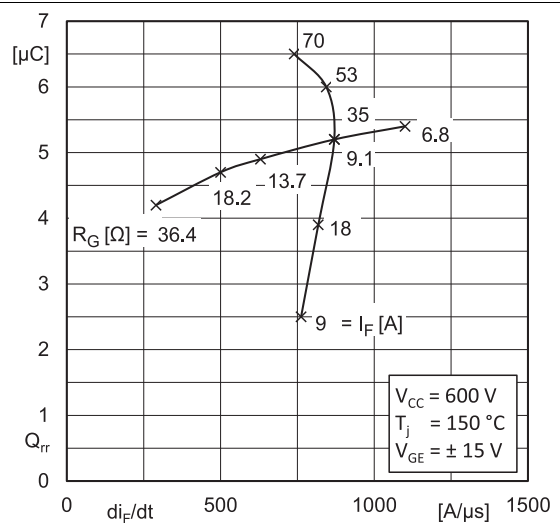
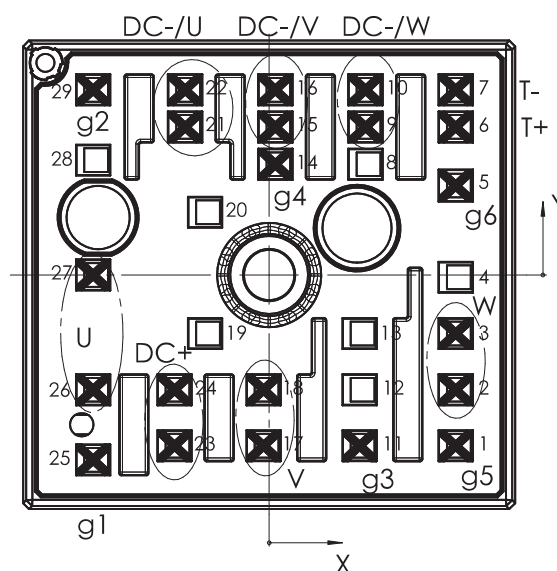


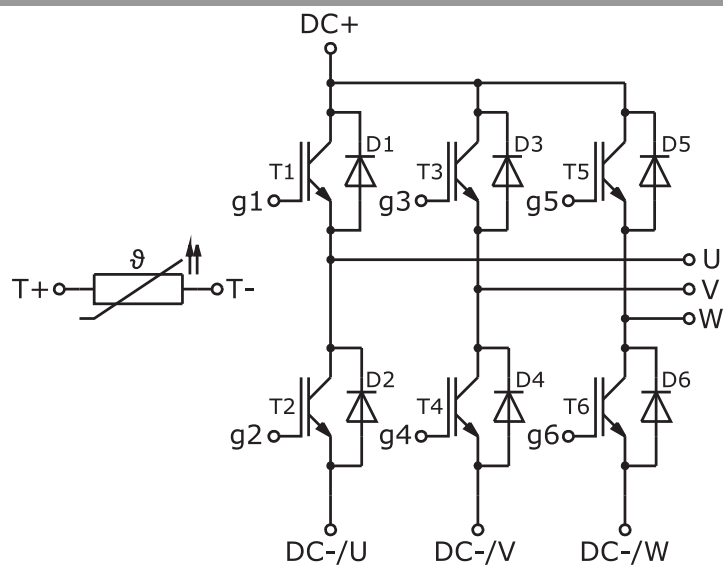
Fig. 12: Typ. CAL diode recovery charge

Pin out							
Pin	X	Y	Function	Pin	X	Y	Function
1	15,93	-14,6	g5	16	0,53	15,8	DC-/V
2	15,93	-9,8	W	17	-0,48	-14,6	V
3	15,93	-5	W	18	-0,48	-9,8	V
4				19			
5	15,93	7,63	g6	20			
6	15,93	12,63	T+	21	-7,18	12,63	DC-/U
7	15,93	15,8	T-	22	-7,18	15,8	DC-/U
8				23	-8,08	-14,6	DC+
9	8,23	12,63	DC-/W	24	-8,08	-9,8	DC+
10	8,23	15,8	DC-/W	25	-15,03	-15,8	g1
11	7,73	-14,6	g3	26	-15,03	-9,8	U
12	7,73	-9,8		27	-15,03	0	U
13				28			
14	0,53	9,45	g4	29	-15,03	15,8	g2
15	0,53	12,63	DC-/V				

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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